

Hongpo Hu

List of Publications by Year in descending order

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9
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422
citing authors

#	ARTICLE	IF	CITATIONS
1	Strain management and AlN crystal quality improvement with an alternating V/III ratio AlN superlattice. Applied Physics Letters, 2021, 118, .	3.3	19
2	Boosted ultraviolet electroluminescence of InGaN/AlGaIn quantum structures grown on high-index contrast patterned sapphire with silica array. Nano Energy, 2020, 69, 104427.	16.0	150
3	Growth of high-quality AlN films on sapphire substrate by introducing voids through growth-mode modification. Applied Surface Science, 2020, 518, 146218.	6.1	43
4	Strategically constructed patterned sapphire with silica array to boost substrate performance in GaN-based flip-chip visible light-emitting diodes. Optics Express, 2020, 28, 38444.	3.4	12
5	Effect of strain relaxation on performance of InGaIn/GaN green LEDs grown on 4-inch sapphire substrate with sputtered AlN nucleation layer. Scientific Reports, 2019, 9, 3447.	3.3	42
6	Heteroepitaxial Growth of High-Quality and Crack-Free AlN Film on Sapphire Substrate with Nanometer-Scale-Thick AlN Nucleation Layer for AlGaIn-Based Deep Ultraviolet Light-Emitting Diodes. Nanomaterials, 2019, 9, 1634.	4.1	12
7	High quality GaN buffer layer by isoelectronic doping and its application to 365nm InGaIn/AlGaIn ultraviolet light-emitting diodes. Applied Surface Science, 2019, 471, 231-238.	6.1	76
8	A Comparative Study of GaN-Based Direct Current and Alternating Current High Voltage Light-Emitting Diodes. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700554.	1.8	5
9	Effects of GaN/AlGaIn/Sputtered AlN nucleation layers on performance of GaN-based ultraviolet light-emitting diodes. Scientific Reports, 2017, 7, 44627.	3.3	92